Thyristor Semiconductor Device - Page 1 of 2



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Inclosure Material:

Metal

Overall Length:

Between 0.300 inches and 0.425 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

Between 0.424 inches and 0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

300.0 reverse voltage, peak

Current Rating Per Characteristic:

2.00 amperes source cutoff current preset

Power Rating Per Characteristic:

20.0 watts small-signal input power, common-collector blank

Maximum Operating Tempurature Per Measurement Point:

100.0 degrees celsius junction

Special Features:

Junction pattern arrangement: pnpn

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

2 tab, solder lug and 1 threaded stud

Specification Data:

81349-mil-s-19500/372 government specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

NSN 5961-00-165-2902

Thyristor Semiconductor Device - Page 2 of 2

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